

RF power transistor - LdmoST family

Preliminary Data

Features

- Excellent thermal stability
- Common source configuration
- P_{OUT} = 25 W with 16 dB gain @ 945 MHz / 13.6 V
- BeO free package
- ESD protection
- In compliance with the 2002/95/EC european directive

Description

The PD85025C is a common source N-channel, enhancement-mode lateral Field-Effect RF power transistor. It is designed for high gain, broadband commercial and industrial applications. It operates at 13.6 V in common source mode at frequencies of up to 1 GHz. PD85025C boasts the excellent gain, linearity and reliability of ST's latest LDMOS technology.

PD85025C's superior linearity performance makes it an ideal solution for mobile application.

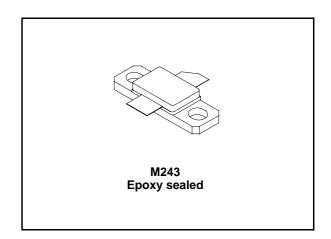


Figure 1. Pin connection

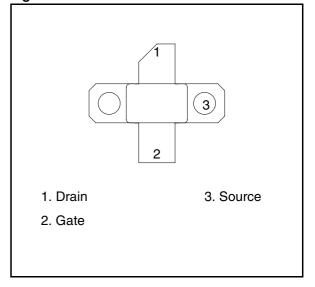


Table 1. Device summary

Order code	Package	Packing
PD85025C	M243	Вох

Contents PD85025C

Contents

1	Elect	trical data	3
	1.1	Maximum ratings	
	1.2	Thermal data	3
2	Elect	trical characteristics	4
	2.1	Static	
	2.2	Dynamic	4
	2.3	ESD protection characteristics	4
3	Impe	edance	5
4	Туріс	cal performance	6
5	Pack	age mechanical data	8
6	Revi	sion history	9

PD85025C Electrical data

1 Electrical data

1.1 Maximum ratings

Table 2. Absolute maximum ratings $(T_{CASE} = 25^{\circ}C)$

Symbol	Parameter	Value	Unit
V _{(BR)DSS}	Drain-source voltage	40	V
V_{GS}	Gate-source voltage	±20	V
I _D	Drain current	7	Α
P _{DISS}	Power dissipation (@ T _C = 70 °C)	93	W
T _J	Max. operating junction temperature	200	°C
T _{STG}	Storage temperature	-65 to +150	°C

1.2 Thermal data

Table 3. Thermal data

Symbol	Parameter	Value	Unit
R _{thJC}	Junction - case thermal resistance	1.4	°C/W

Electrical characteristics PD85025C

2 Electrical characteristics

$$T_{CASE} = +25$$
 °C

2.1 Static

Table 4. Static

Symbol		Test conditions	Min	Тур	Max	Unit	
I _{DSS}	$V_{GS} = 0 V$	V _{DS} = 25 V				1	μΑ
I _{GSS}	V _{GS} = 20 V	$V_{DS} = 0 V$				1	μΑ
V _{GS(Q)}	V _{DS} = 10 V	I _D = TBD mA			TBD		V
V _{DS(ON)}	V _{GS} = 10 V	I _D = 1 A			270	310	mV
C _{ISS}	V _{GS} = 0 V	V _{DS} = 12.5 V	f = 1 MHz		49		pF
C _{OSS}	V _{GS} = 0 V	V _{DS} = 12.5 V	f = 1 MHz		35		pF
C _{RSS}	V _{GS} = 0 V	V _{DS} = 12.5 V	f = 1 MHz		1.0		pF

2.2 Dynamic

Table 5. Dynamic

Symbol	Test conditions		Тур.	Max.	Unit
P3dB	$V_{DD} = 13.6 \text{ V}, I_{DQ} = 300 \text{ mA}$ f = 945 MHz	25	30		W
G _P	$V_{DD} = 13.6 \text{ V}$, $I_{DQ} = 300 \text{ mA}$, $P_{OUT} = 10 \text{ W}$, $f = 945 \text{ MHz}$	15	17.5		dB
h _D	$V_{DD} = 13.6 \text{ V}, I_{DQ} = 300 \text{ mA}, P_{OUT} = P3dB, f = 945 \text{ MHz}$	60	73		%
Load mismatch	V_{DD} = 17 V, I_{DQ} = 300 mA, P_{OUT} = 45 W, f = 945 MHz All phase angles	20:1			VSWR

2.3 ESD protection characteristics

Table 6. ESD protection characteristics

Test conditions	Class
Human body model	2
Machine model	M3

PD85025C Impedance

3 Impedance

Figure 2. Current conventions

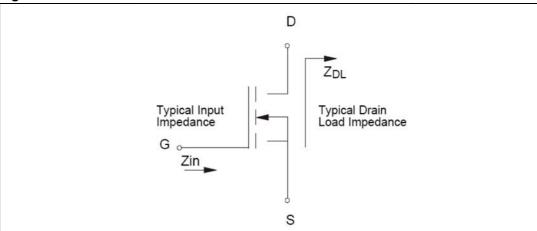
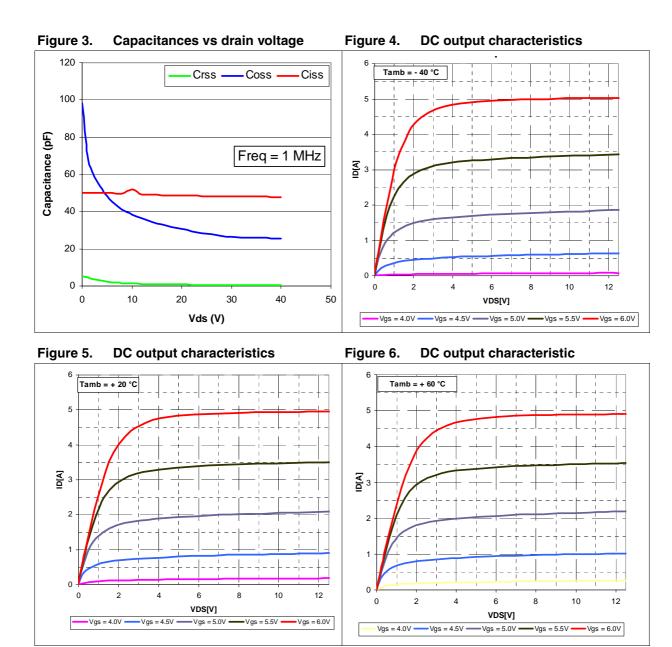


Table 7. Impedance data

Freq. (MHz)	Z _{IN} (Ω)	$Z_DL(\Omega)$
945 MHz	1.01 + j 2.03	1.75 + j 2.20

Typical performance PD85025C

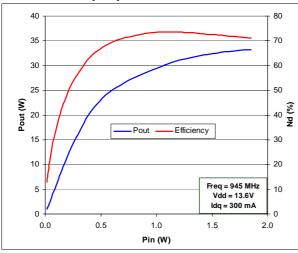
4 Typical performance



6/10

Figure 7. Output power and efficiency vs input power

Figure 8. Gain vs output power and bias current



22 -400mA 100mA --300mA 200mA 18 Gain (dB) Freq = 945 MHz 14 Vdd = 13.6V12 10 0 10 20 25 30 35 40 Pout (W)

Figure 9. Pout and drain current vs gate voltage

Figure 10. Pout and drain current vs supply voltage

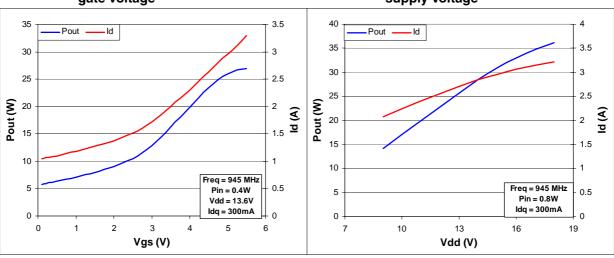
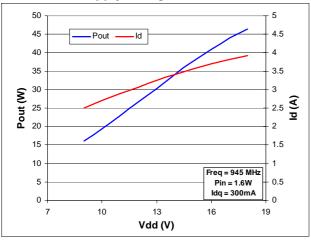


Figure 11. Pout and drain current vs supply voltage



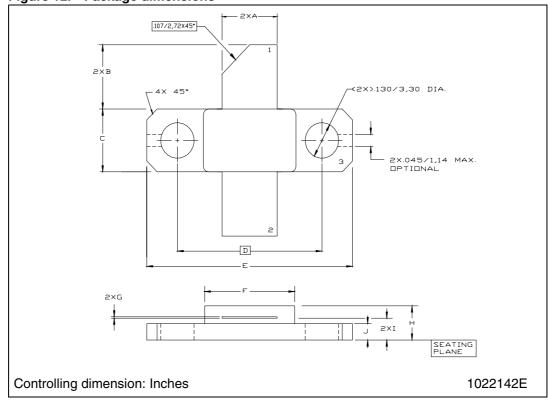
5 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

Table 8.	M243 (.230 x .360 2L N/HERM W/FLG) mechanical data
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Dim.	mm.				Inch	
	Min	Тур	Max	Min	Тур	Max
Α	5.21		5.72	0.205		0.225
В	5.46		6.48	0.215		0.255
С	5.59		6.10	0.220		0.240
D		14.27			0.562	
Е	20.07		20.57	0.790		0.810
F	8.89		9.40	0.350		0.370
G	0.10		0.15	0.004		0.006
Н	3.18		4.45	0.125		0.175
I	1.83		2.24	0.072		0.088
J	1.27		1.78	0.050		0.070

Figure 12. Package dimensions



PD85025C Revision history

6 Revision history

Table 9. Document revision history

Date	Revision	Changes
10-Dec-2007	1	Initial release.

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